

# DMG204B0

Silicon NPN epitaxial planar type (Tr1)  
Silicon PNP epitaxial planar type (Tr2)

For low frequency amplification

■ Features

- High forward current transfer ratio  $h_{FE}$  with excellent linearity
- Low collector-emitter saturation voltage  $V_{CE(sat)}$
- Halogen-free / RoHS compliant  
(EU RoHS / UL-94 V-0 / MSL: Level 1 compliant)

■ Marking Symbol: C4

■ Basic Part Number

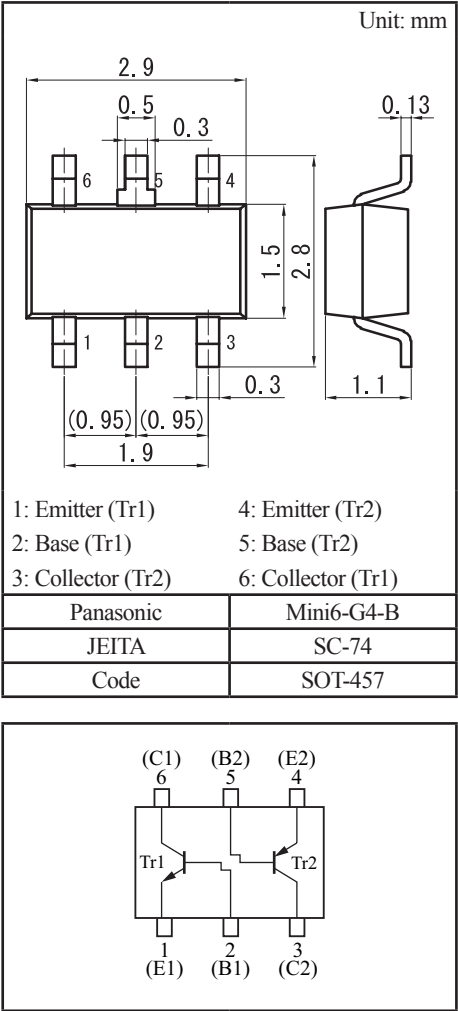
DSC2001 + DSA2401 (Individual)

■ Packaging

DMG204B00R Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)

■ Absolute Maximum Ratings  $T_a = 25^{\circ}\text{C}$

Parameter		Symbol	Rating	Unit
Tr1	Collector-base voltage (Emitter open)	$V_{CBO}$	60	V
	Collector-emitter voltage (Base open)	$V_{CEO}$	50	V
	Emitter-base voltage (Collector open)	$V_{EBO}$	7	V
	Collector current	$I_C$	100	mA
	Peak collector current	$I_{CP}$	200	mA
Tr2	Collector-base voltage (Emitter open)	$V_{CBO}$	−15	V
	Collector-emitter voltage (Base open)	$V_{CEO}$	−10	V
	Emitter-base voltage (Collector open)	$V_{EBO}$	−7	V
	Collector current	$I_C$	−0.5	A
	Peak collector current	$I_{CP}$	−1	A
Overall	Total power dissipation	$P_T$	300	mW
	Junction temperature	$T_j$	150	°C
	Operating ambient temperature	$T_{opr}$	−40 to +85	°C
	Storage temperature	$T_{stg}$	−55 to +150	°C



■ Electrical Characteristics  $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

• Tr1

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	$V_{\text{CBO}}$	$I_{\text{C}} = 10 \mu\text{A}, I_{\text{E}} = 0$	60			V
Collector-emitter voltage (Base open)	$V_{\text{CEO}}$	$I_{\text{C}} = 2 \text{ mA}, I_{\text{B}} = 0$	50			V
Emitter-base voltage (Collector open)	$V_{\text{EBO}}$	$I_{\text{E}} = 10 \mu\text{A}, I_{\text{C}} = 0$	7			V
Collector-base cutoff current (Emitter open)	$I_{\text{CBO}}$	$V_{\text{CB}} = 20 \text{ V}, I_{\text{E}} = 0$			0.1	$\mu\text{A}$
Collector-emitter cutoff current (Base open)	$I_{\text{CEO}}$	$V_{\text{CE}} = 10 \text{ V}, I_{\text{B}} = 0$			100	$\mu\text{A}$
Forward current transfer ratio	$h_{\text{FE}}$	$V_{\text{CE}} = 10 \text{ V}, I_{\text{C}} = 2 \text{ mA}$	210		460	—
Collector-emitter saturation voltage	$V_{\text{CE(sat)}}$	$I_{\text{C}} = 100 \text{ mA}, I_{\text{B}} = 10 \text{ mA}$		0.13	0.3	V
Transition frequency	$f_{\text{T}}$	$V_{\text{CE}} = 10 \text{ V}, I_{\text{C}} = 2 \text{ mA}$		150		MHz
Collector output capacitance (Common base, input open circuited)	$C_{\text{ob}}$	$V_{\text{CB}} = 10 \text{ V}, I_{\text{E}} = 0, f = 1 \text{ MHz}$		1.5		pF

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

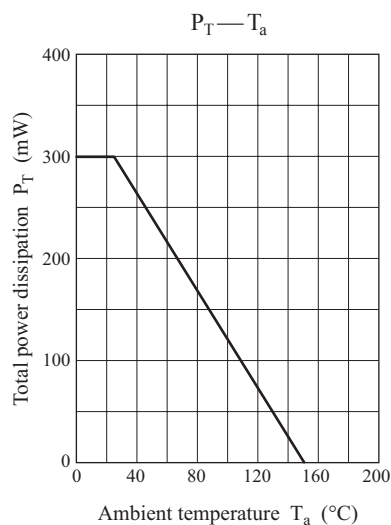
• Tr2

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	$V_{\text{CBO}}$	$I_{\text{C}} = -10 \mu\text{A}, I_{\text{E}} = 0$	-15			V
Collector-emitter voltage (Base open)	$V_{\text{CEO}}$	$I_{\text{C}} = -1 \text{ mA}, I_{\text{B}} = 0$	-10			V
Emitter-base voltage (Collector open)	$V_{\text{EBO}}$	$I_{\text{E}} = -10 \mu\text{A}, I_{\text{C}} = 0$	-7			V
Collector-base cutoff current (Emitter open)	$I_{\text{CBO}}$	$V_{\text{CB}} = -10 \text{ V}, I_{\text{E}} = 0$			-100	nA
Forward current transfer ratio *1	$h_{\text{FE1}}$	$V_{\text{CE}} = -2 \text{ V}, I_{\text{C}} = -0.5 \text{ A}$	130		350	—
	$h_{\text{FE2}}$	$V_{\text{CE}} = -2 \text{ V}, I_{\text{C}} = -1 \text{ A}$	60			
Collector-emitter saturation voltage *1	$V_{\text{CE(sat)}}$	$I_{\text{C}} = -0.4 \text{ A}, I_{\text{B}} = -8 \text{ mA}$		-0.15	-0.30	V
Base-emitter saturation voltage *1	$V_{\text{BE(sat)}}$	$I_{\text{C}} = -0.4 \text{ A}, I_{\text{B}} = -8 \text{ mA}$		-0.8	-1.2	V
Transition frequency	$f_{\text{T}}$	$V_{\text{CE}} = -10 \text{ V}, I_{\text{C}} = -50 \text{ mA}$		250		MHz
Collector output capacitance (Common base, input open circuited)	$C_{\text{ob}}$	$V_{\text{CB}} = -10 \text{ V}, I_{\text{E}} = 0, f = 1 \text{ MHz}$		18		pF

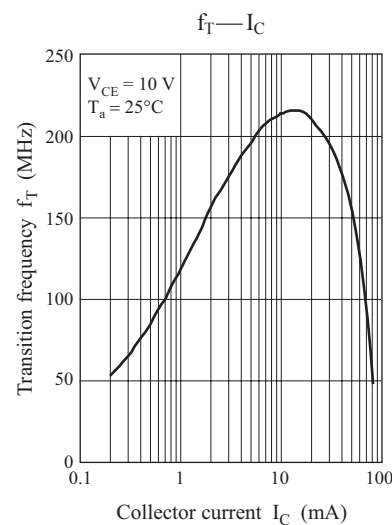
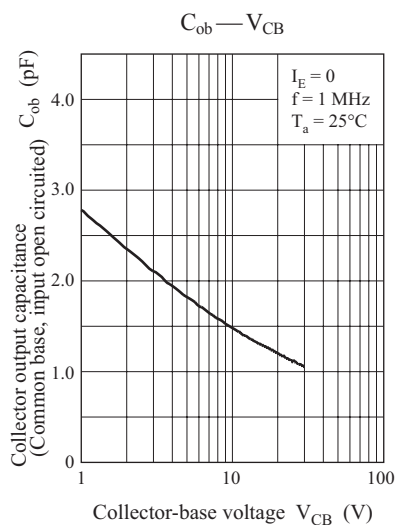
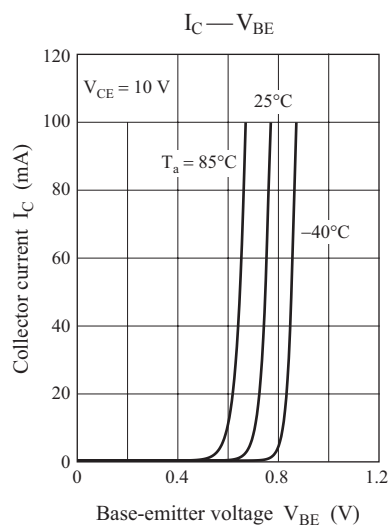
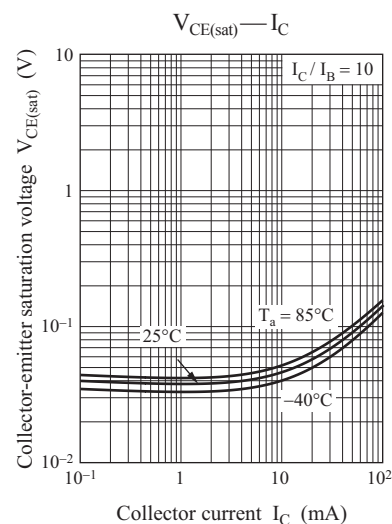
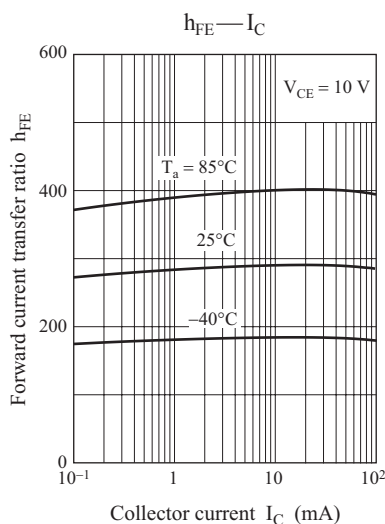
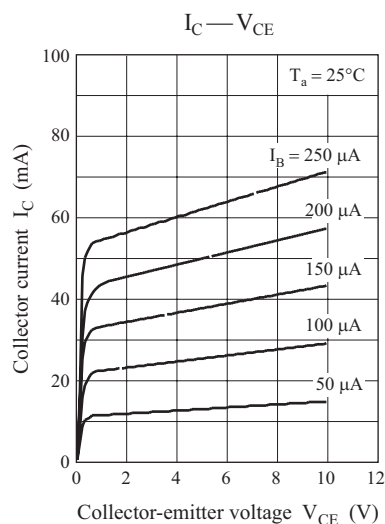
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. \*1: Pulse measurement

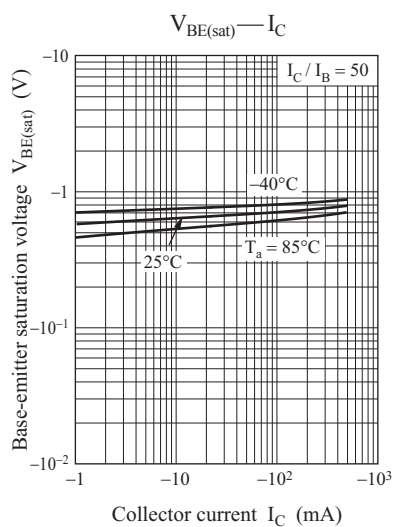
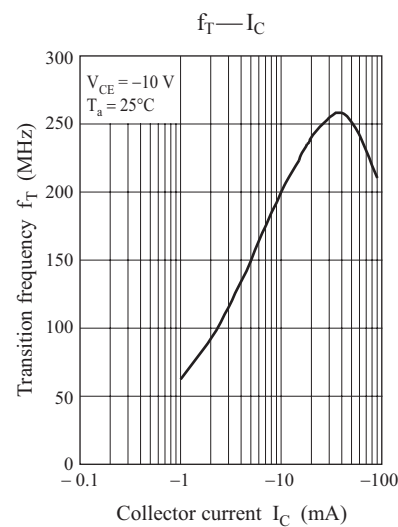
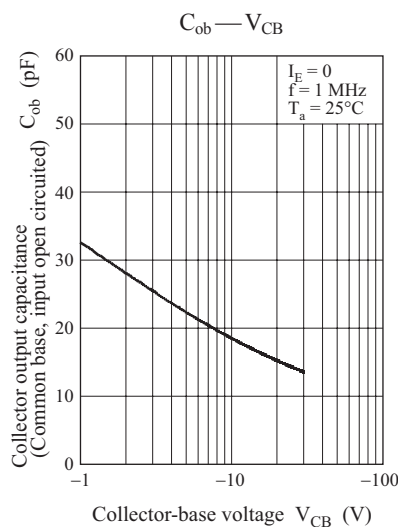
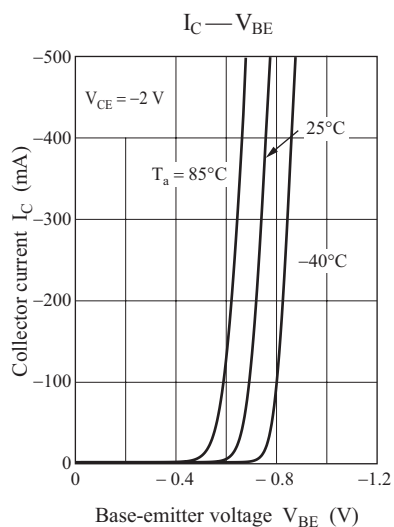
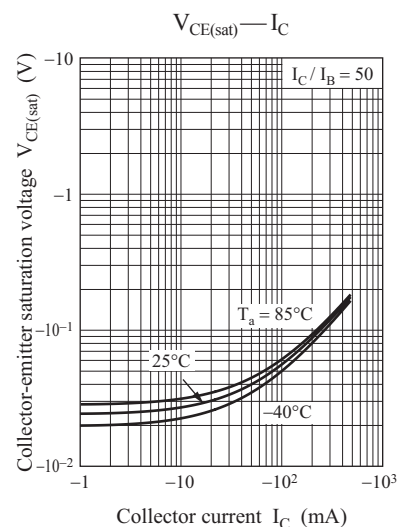
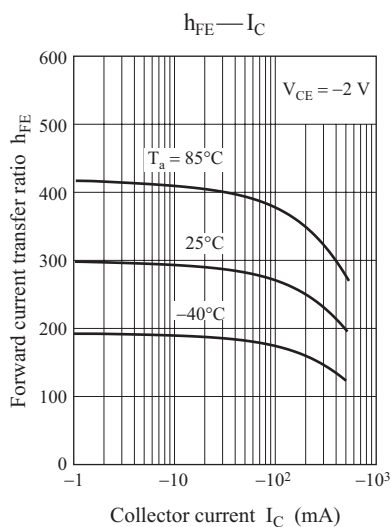
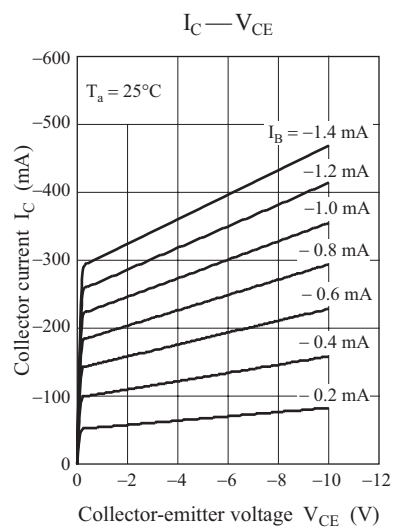
Common characteristics chart



Characteristics charts of Tr1



## Characteristics charts of Tr2





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